

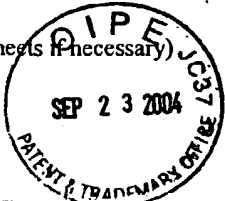
<b>FORM PTO-1449</b> U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number 5308-157IP2		Serial No. 10/045,542	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Das et al.			
				Filing Date: October 26, 2001		Group 1762	
<b>U. S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
KCG	1.	International Preliminary Examination Report issued August 4, 2003 for corresponding PCT application no. PCT/US02/11691.					

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*Kirsten Colley*

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kg	1	Wang et al. "The Effects of NH <sub>3</sub> Plasma Passivation on Polysilicon Thin-Film Transistors," <i>IEEE Electron Device Letters</i> , Vol. 16, No. 11, November 1995, pp. 503-5.					

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Ycj	1	Williams et al., "Passivation of the 4-H SiC/SiO <sub>2</sub> Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.
Ycj	2	Chung et al., "Effects of Anneals in Ammonia on the Interface Trap Density Near the Band Edges in 4H-Silicon Carbide Metal-Oxide-Semiconductor Capacitors", <i>Applied Physics Letters</i> , Vol. 77, No. 22, November 27, 2000, pp. 3601-3603.

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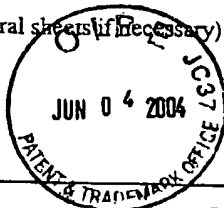
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Serial No.  
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Filing Date: October 26, 2001

Group  
1762

U. S. PATENT DOCUMENTS

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	1	5,587,870	12/24/96	Anderson et al.	361	313	
	2	5,877,045	3/2/99	Kapoor	438	151	

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes   No
	3	WO99/63591	12/9/99	PCT	—	—	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	4	Mutin, P. Herbert, "Control of the Composition and Structure of Silicon Oxycarbide and Oxynitride Glasses Derived from Polysiloxane Precursors," <i>Journal of Sol-Gel Science and Technology</i> . Vol. 14 (1999) pp. 27-38.
	5	del Prado et al. "Full Composition Range Silicon Oxynitride Films Deposited by ECR-PECVD at Room Temperatures," <i>Thin Solid Films</i> . Vol. 343-344 (1999) p. 437-440.
FCJ	6	Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," <i>IEEE Transactions on Electron Devices</i> . Vol. 47, No. 2, February 2000.
	7	International Search Report for PCT/US02/09393 dated 10/15/03.

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	2	5,739,564	04/14/98	Kosa et al.	257	298	
	3	6,228,720	05/08/01	Kitabatake et al.	438	268	
	4	6,239,463	05/29/01	Williams et al.	257	328	
	5	6,316,791	11/13/01	Schomer et al.	257	77	
	6	6,593,620	07/15/03	Hshieh et al.	257	335	
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	7	WO 98/02924	01/22/98	PCT	—	—	
	8	WO 00/13236	03/09/00	PCT	—	—	
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	9	Dimitrijevic et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177.					
	10	De Mao et al., "Thermal Oxidation of SiC in N <sub>2</sub> O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.					
	11	Ryu et al., Article and Presentation: "27 mΩ-cm <sup>2</sup> , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices &amp; ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.					

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already on 1449	1	Williams et al., "Passivation of the 4-H SiC/SiO <sub>2</sub> Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.
already on 1449 on 2/6/04	2	Chung et al., "Effects of Anneals in Ammonia on the Interface Trap Density Near the Band Edges in 4H-Silicon Carbide Metal-Oxide-Semiconductor Capacitors", <i>Applied Physics Letters</i> , Vol. 77, No. 22, November 27, 2000, pp. 3601-3603.


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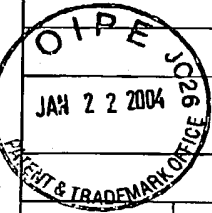
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